



SURFACE MOUNT
NPN Digital Silicon Transistor

CHEMG3GP

* G3

SOT553

Dimensions in millimeters

SOT553

CIRCUIT

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-Base voltage		50	V
V _{CE0}	Collector-Emitter voltage		50	V
V _{EB0}	Emitter-Base voltage		5	V
I _{C(Max.)}	Collector current		100	mA
P _D	Power dissipation	T _{amb} ≤ 25 °C, Note 1	150	mW
T _{STG}	Storage temperature		−55 +150	°C
T _J	Junction temperature		150	°C

Note

2004-07

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHEMG3GP)

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BV _{CBO}	Collector-Base breakdown voltage	I _C =50uA	50.0	–	–	V
BV _{CEO}	Collector-Emitter breakdown voltage	I _C =1mA	50.0	–	–	V
BV _{EBO}	Emitter-Base breakdown voltage	I _E =50uA	5.0	–	–	V
V _{CE(sat)}	Collector-Emitter Saturation voltage	I _C =5mA; I _B =0.25mA	–	–	0.3	V
I _{CBO}	Collector-Base current	V _{CB} =50V	–	–	0.5	uA
I _{EBO}	Emitter-Base current	V _{EB} =4V	–	–	0.5	uA
h _{FE}	DC current gain	I _C =1mA; V _{CE} =5.0V	100	250	600	
R ₁	Input resistor		3.29	4.7	6.11	KΩ
f _T	Transition frequency	I _E =-5mA, V _{CE} =10.0V f=100MHz	–	250	–	MHz

Note

1.Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHEMG3GP)

Typical Electrical Characteristics

Fig.1 DC current gain vs. collector current

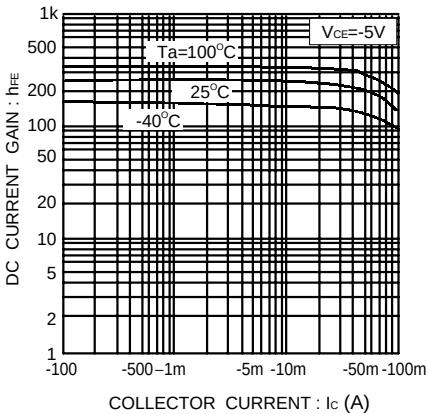


Fig.2 Collector-emitter saturation voltage vs. collector current

